IN THE SPECIFICATION:

Paragraph beginning at line 13 of page 6 has been amended as follows:

In the processing method of the present invention, there is implemented irradiation with a charged particle beam in such a manner that, when executing processing in a uniform manner matter, when deposition processing or etching processing of a prescribed pattern is carried out using a charged particle beam apparatus, a region of the pattern to be processed is divided up into microscopic regions having a size corresponding to each being slightly smaller in size than the diameter of the beam, such that when the beam irradiates a respective microscopic region it also irradiates portions of adjacent microscopic regions, and regulation is performed by scanning circuits etc. with processing proceeding simultaneously for a plurality of patterns within the scanning region in such a manner that the dose amount for each microscopic region becomes equal.